

ABSTRACT

An electric semiconductor component includes a monocrystalline semiconductor substrate made of silicon, for example, an insulation layer arranged on the surface of the semiconductor substrate and penetrated by a contact hole in at least one location and a contact element that contacts the semiconductor substrate through the contact hole and is made of a material in which the semiconductor material of the substrate is soluble in an anisotropic dissolving process. The edges of the contact hole are configured as diffusion stop structures.